

Features

- 2.5/3.3V supply voltage
- 4 HCSL 100/125/200/250MHz outputs with OE
- 2 LVCMOS 33/50/66/100MHz selectable outputs
- 5 LVCMOS 25MHz or 125MHz outputs
- 1 LVPECL 312.5MHz, 156.25MHz or 125MHz output
- 1 CMOS 156.25MHz or 125MHz output
- 1 LVPECL 125MHz or 25MHz output
- 25MHz crystal or differential input
- 0.5ps (typ) RMS integrated phase noise design at 3.3V operation
- 1.0ps (typ) RMS integrated phase noise design at 2.5V operation
- PLL Bypass mode for test
- Industrial Temperature -40°C to 85°C
- TQFN - 56 package

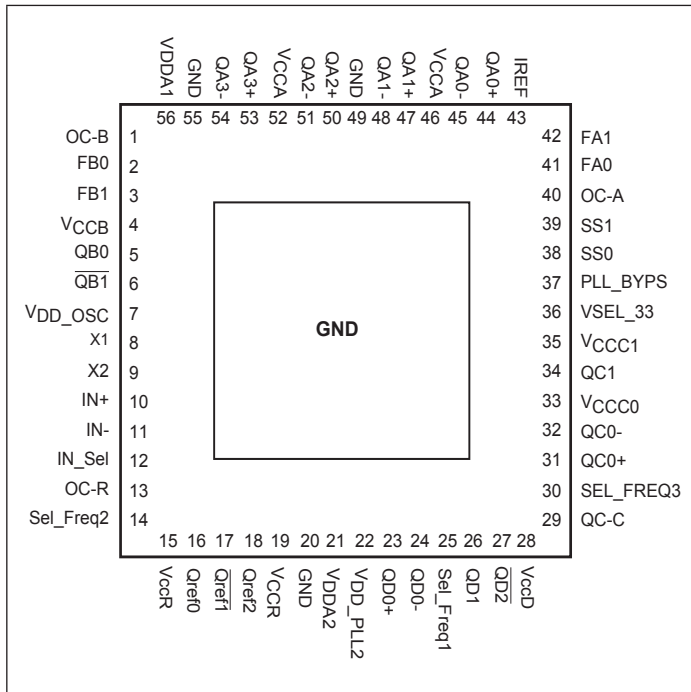
Description

The PI6LC4833 implements Pericom's advanced LC VCO technology and is specifically designed for Power PC network processor (Freescale MPC8548, MPC8572, AMCC 460, AMI732). This high performance device is optimized to generate CPU core/PCI clock, high performance PCIe Gen1/2 Clock, SRIO, Gigabit Ethernet's MAC and PHY clock. All outputs are generated from 25MHz external clock input or crystal.

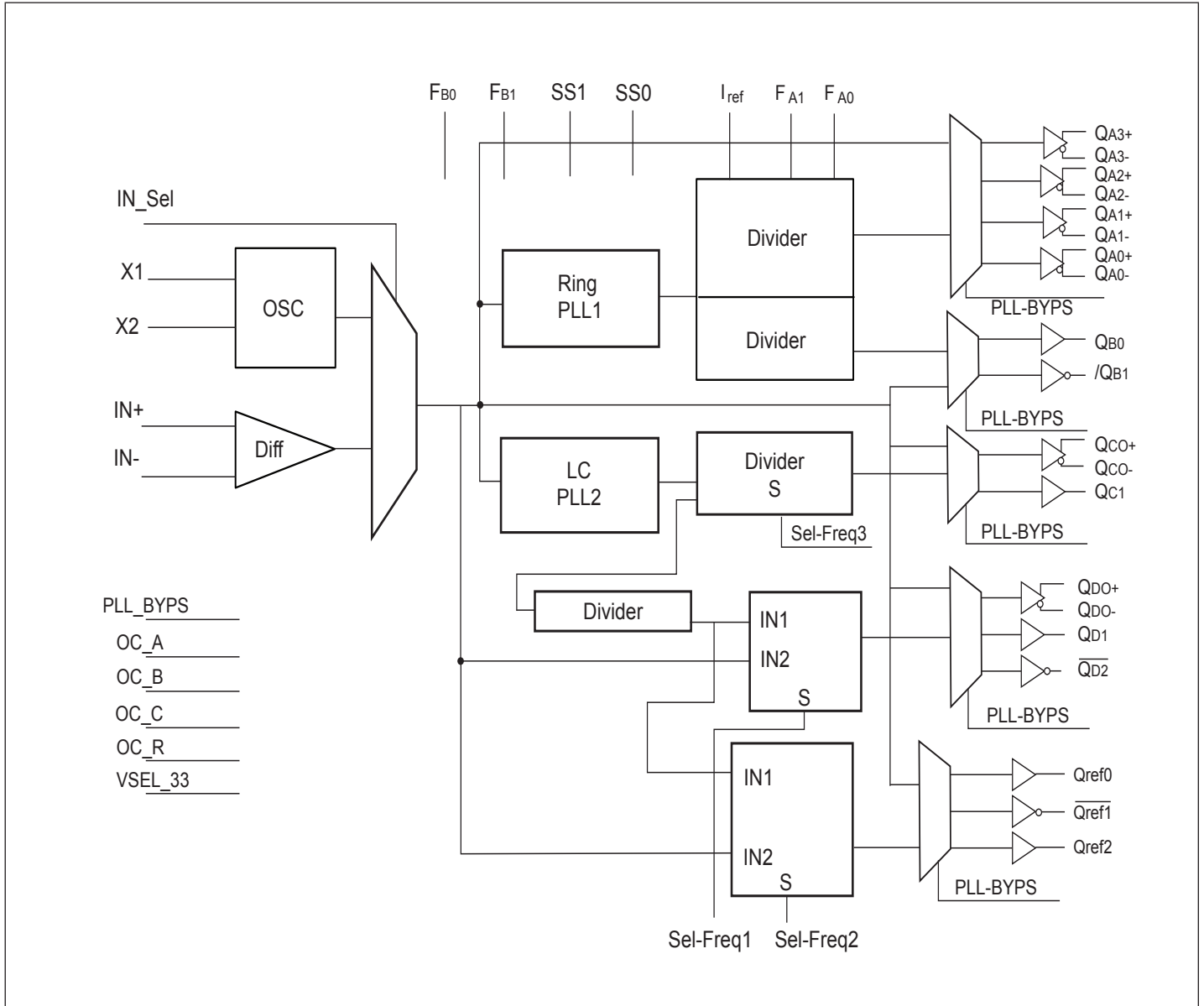
Application

- Router/Switch
- OLT, BSC, WLAN, Wireless gateway
- Wireless

Pin Configuration (56-Pin TQFN)



Block Diagram



Pinout Table

Pin Number	Pin Name	I/O Type	Description
44, 45, 47, 48, 50, 51, 53, 54	Q _{A0+} , Q _{A0-} , Q _{A1+} , Q _{A1-} , Q _{A2+} , Q _{A2-} , Q _{A3+} , Q _{A3-}	Output	100/125/200/250MHz HCSL Outputs
5, 6	Q _{B0} , \overline{Q}_{B1}	Output	33/50/66/100MHz LVCMOS Outputs
8	X1	Input	Crystal Input Pin
9	X2	Output	Oscillator Output Pin
10, 11	IN+, IN-	Input	HCSL/LVPECL/LVDS Inputs
12	IN_Sel	Input	Low: X1 and X2 are selected. High: IN+ and IN- are selected. The pin has an internal pull-up resistor of 100k Ω .
37	PLL_BYPS	Input	Low: Output buffers are switched to the PLL. High: Output buffers are switched to the input mux. The pin has an internal pull-down resistor of 100k Ω .
40, 1, 29, 13	OC_A, OC_B, OC_C, OC_R	Input	Low: Outputs are enabled. High: High impedance mode is selected. The pin has an internal pull-down resistor of 100k Ω .
7	V _{DD_OSC}	Power	Power for crystal OSC core
21	V _{DDA2}	Power	Power for LC PLL2
46, 52, 4, 33, 35, 28, 15, 19	V _{ccA} , V _{ccB} , V _{ccC0} , V _{ccC1} V _{ccD} , V _{ccR}	Power	Power for output buffers (Q _A , Q _B , Q _C , Q _D , Q _{ref})
56	V _{DDA1}	Power	Power for Ring PLL1
20, 49, 55	GND	Power	Ground includes external paddle (EPAD).
34, 31, 32	Q _{C1} , Q _{C0+} / Q _{C0-}	Output	125MHz/156.25MHz/312.5MHz LVCMOS and LVPECL
16, 17, 18, 23, 24, 26, 27	Q _{ref0} , \overline{Q}_{ref1} , Q _{ref2} , Q _{D0+} /Q _{D0-} , Q _{D1} , \overline{Q}_{D2}	Output	25MHz or 125MHz LVCMOS, or LVPECL (Q _{D0+} /Q _{D0-})
42, 41	F _{A1} , FA0	Input	Q _A Bank Output Frequency Selection (see function table). This pin has a built-in pull-down resistor of 100k Ω .
3, 2	F _{B1} , FB0	Input	Q _B Bank Output Frequency Selection (see function table). This pin has a built-in pull-up resistor of 100k Ω .
25	Sel_Freq1	Input	Low: Q _D 25MHz Output High: Q _D 125MHz Output This pin has a built-in pull-up resistor of 100k Ω .
22	V _{DD_PLL2}	Power	Power for PLL2 Core
14	Sel_Freq2	Input	Low: Q _{ref} 25MHz Output High: 125MHz Output This pin has a built-in pull-down resistor of 100k Ω .

Pin Number	Pin Name	I/O Type	Description
30	Sel_Freq3	Input	Low: Q _C 156.25MHz Output High: 125MHz Output Floating: Output 312.5MHz (Q _{C1} is HiZ if floating) This pin has a built-in pull-up resistor of 150kΩ and pull-down resistor of 100kΩ.
39, 38	SS1, SS0	Input	Spread Selection Pin for Q _A and Q _B This pin has a built-in pull-up resistor of 100kΩ (see function table).
43	I _{REF}	Input	External resistor connection for internal current reference
36	VSEL_33	Input	Low: 2.5V mode, High: 3.3V mode This pin has a built-in pull_up resistor of 100kΩ

Function Table

Output	Buffer	Frequency (MHz)	Selection Pin
Q _{A0+/-} , Q _{A1+/-} , Q _{A2+/-} , Q _{A3+/-}	HCSL x4	100, 125, 200, 250	F _{A1} , F _{A0}
\overline{Q}_{B1} , Q _{B0}	CMOS x2	33.3333, 50, 66.6667, 100	F _{B1} , F _{B0}
Q _{C0+/-}	LVPECL x1	125, 156.25, 312.5	Sel_Freq3
Q _{C1}	CMOS x1	125, 156.25, HiZ	
Q _{D0+/-}	LVPECL x1	25, 125	Sel_Freq1
\overline{Q}_{D2} , Q _{D1}	CMOS x2	25, 125	
Q _{ref2} , \overline{Q}_{ref1} , Q _{ref0}	CMOS x3	25, 125	Sel_Freq2

F _{B1}	F _{B0}	Q _{B0}	\overline{Q}_{B1}	Output
0	0	33.33MHz	33.33MHz	LVC MOS
0	1	66.66MHz	66.66MHz	LVC MOS
1	0	100MHz	100MHz	LVC MOS
1	1	50MHz	50MHz	LVC MOS

F _{A1}	F _{A0}	Q _{A0+} / Q _{A0-}	Q _{A1+} / Q _{A1-}	Q _{A2+} / Q _{A2-}	Q _{A3+} / Q _{A3-}
0	0	100MHz	100MHz	100MHz	100MHz
0	1	125MHz	125MHz	125MHz	125MHz
1	0	200MHz	200MHz	200MHz	200MHz
1	1	250MHz	250MHz	250MHz	250MHz

Sel_Freq3	Q _{Cx}	Output_Freq
0	Q _{Cx}	156.25MHz
1	Q _{Cx}	125MHz
NC	Q _{C0}	312.5MHz
	Q _{C1}	HiZ

Sel_Freq1	Q _{D0+} , Q _{D0-}	\bar{Q}_{D2} , Q _{D1}	Output_Freq
0	LVPECL	LVC MOS	25MHz
1	LVPECL	LVC MOS	125MHz

Sel_Freq2	Q _{ref2} , \bar{Q}_{ref1} , Q _{ref0}	Output_Freq
0	LVC MOS	25MHz
1	LVC MOS	125MHz

SS1	SS0	Spread %
0	0	+/- 0.25
0	1	-0.5
1	0	-0.75
1	1	No spread

Note: The SS1 and SS0 pins control the spread ratio of both Q_A and Q_B.

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature.....	-65°C to +155°C
Operating Temperature	-40°C to +85°C
Supply Voltage	-0.5V to 4.6V
ESD Protection (HBM)	2000V

Note: Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Recommended Operating Conditions

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{DD_XX}	OSC, A1, A2, PLL2	2.5V	2.375	-	2.625	V
V _{CC_X}	Q _A , Q _B , Q _C , Q _D , Q _{ref}	2.5V	2.375	-	2.625	V
V _{DD_XX}	OSC, A1, A2, PLL2	3.3V	3.135	-	3.465	V
V _{CC_X}	Q _A , Q _B , Q _C , Q _D , Q _{ref}	3.3V	3.135	-	3.465	V
I _{DD}	Total Power Supply Current	-	-	-	360	mA
I _{DDA1, 2}	Individual Analog PLL Current, V _{DDA1,2}	-	-	-	50	mA
P _{Diss}	Power Dissipation	-	-	-	1250	mW
T _A	Operating Temperature	-	-40	-	+85	°C

LVC MOS DC Electrical Characteristics (Over Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{IH}	Input High Voltage		2	-	V _{DD} +0.3	V
V _{IL}	Input Low Voltage		-0.3	-	0.8	V
V _{OH}	Output High Voltage	I _{OH} = -8mA	V _{DD} -0.4	-	-	V
V _{OL}	Output Low Voltage	I _{OL} = 8mA	-	-	0.4	V
I _{IH}	Input High Current	V _{IN} = V _{DD}	-	-	45	μA
I _{IL}	Input Low Current	V _{IN} = 0V	-45	-	-	μA
R _{PU}	Internal Pull Up Resistance	IN-, IN_SEL, F _{B1} , F _{B0} , Sel_Freq1, SS1, SS0, VSEL_33		100	-	kΩ
		Sel_Freq3		150		kΩ
R _{DN}	Internal Pull Down Resistance	IN+, PLL_BYPS, OC_A, OC_B, OC_C, OC_R, F _{A1} , F _{A0} , Sel_ Freq2, Sel_Freq3		100	-	kΩ
Z _O	Output Impedance	V _{DD} = 2.5V	-	22	-	Ω
		V _{DD} = 3.3V	-	17	-	Ω

LVC MOS AC Characteristics (Over Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
f_{error}	Frequency Synthesis Error	-	-	-	0	ppm	
T_r/T_f	Output Rise/Fall time	20% to 80%, CL =10pF	-	-	3	ns	
T_{DC}	Output Duty Cycle	$t_{DC} = t_H/t_{CY}$, t_H =High Pulse Width, t_{CY} =Output Cycle Time, at $V_{DD}/2$	47	-	53	%	
$t_{jit(CC)}$	Jitter, Cycle-to-Cycle	$V_{DD} = 3.3V$, Q_B , $SS1 = SS0 = 1$	33.33MHz	-	70	110	ps
			66.67MHz	-	80	110	ps
			50MHz	-	70	100	ps
			100MHz	-	80	110	ps
		$V_{DD} = 3.3V$, Q_D, Q_{C1}, Q_{ref}	25MHz	-	80	100	ps
			125MHz/ 156MHz	-	70	100	ps
		$V_{DD} = 2.5V$, Q_B , $SS1 = SS0 = 1$	33.33MHz	-	90	140	ps
			66.67MHz	-	110	130	ps
			50MHz	-	100	120	ps
			100MHz	-	100	120	ps
		$V_{DD} = 2.5V$, Q_D, Q_{C1}, Q_{ref}	25MHz	-	90	120	ps
			125MHz/ 156MHz	-	90	130	ps
Jitter	RMS Phase Jitter	3.3V Operation Q_D, Q_C, Q_{ref} (125MHz), 12k~20MHz $SS1 = SS0 = 1$	-	0.5	-	ps	
		2.5V Operation Q_D, Q_C, Q_{ref} (125MHz), 12k~20MHz $SS1 = SS0 = 1$	-	1	-	ps	

Differential DC Input Characteristics (Over Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _{IH}	Input High Current, IN-	V _{IN} = V _{DD} =3.465V	-	-	5	μA
	Input High Current, IN+		-	-	45	μA
I _{IL}	Input Low Current, IN-	V _{IN} = 0V	-45	-	-	μA
	Input Low Current, IN+		-5	-	-	μA
V _{COMMON}	Common Mode Voltage Range	-	0.2	-	V _{DD} -0.925V	V
V _{PK}	Peak-to-Peak Input Voltage Swing	-	0.15	-	1.3	V

1. V_{IL} should not be less than -0.3V
2. Common mode voltage is defined as the cross point of the differential signal

HCSL DC Electrical Characteristics (Over Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{OH}	Output High Voltage	All frequencies except at 250MHz	660	-	850	mV
		Only at 250MHz	600	-	850	mV
V _{OL}	Output Low Voltage	-	-	-	150	mV
V _{CROSS}	Absolute Crossing Point Voltages	-	250	-	550	mV
ΔV _{CROSS}	Total Variation of V _{CROSS} Overall Edges	-	-	-	140	mV
I _{OH}	Output High Current with 475-Ohm resistor. Connected between I _{REF} pin and GND	-	-	15	-	mA

HCSL AC Switching Characteristics ^(1, 2, 3) (Over Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
f_{error}	Frequency Synthesis Error	-	-	-	0	ppm
T_r / T_f	Output Rise/Fall time (measured between 0.175V to 0.525V) ²	-	175	-	700	ps
$\Delta T_r / \Delta T_f$	Rise and Fall Time Variation ²	-	-	-	125	ps
T_{skew}	Output-to-Output Skew ³	-	-	-	50	ps
T_{DC}	Output Duty Cycle ³	-	47	-	53	%
J_{HF-RMS}	>1.5MHz-50MHz RMS jitter applying PCIe G2 jitter mask ³	SS1= SS0 = 1	-	-	3.1	ps
	Using PCIe G3 jitter mask ³	SS1= SS0 = 1, Low Frequency	-	-	3.0	ps
		SS1= SS0 = 1, High Frequency	-	0.5	1.0	ps
PSRR	Power Supply Noise Rejection Ratio with 20mVp-p Input Sine Wave 100kHz to 600kHz ²	-	-	-50	-	dBc
PLL _{LBW}	PLL Loop Bandwidth	-	-	350	-	kHz

1. Test configuration is $R_s=33\Omega$, $R_p=49.9\Omega$, and 2pF
2. Measurement taken from Single-Ended Waveform
3. Measurement taken from Differential Waveform

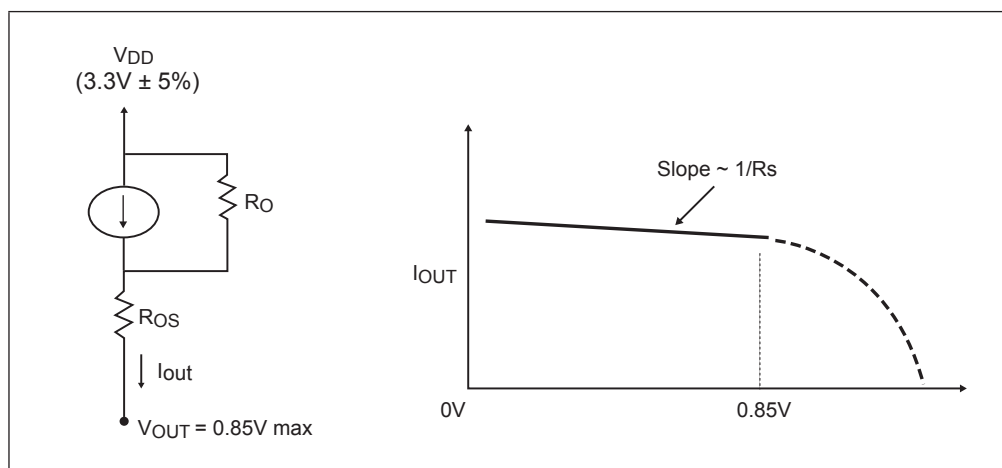
LVPECL DC Electrical Characteristics (Over Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{PP}	Output peak-peak Voltage	-	0.4	-	1	V
V_{OH}	Output High Voltage	-	$V_{DD}-1.2$	-	$V_{DD}-0.7$	V
V_{OL}	Output Low Voltage	-	$V_{DD}-1.85$	-	$V_{DD}-1.55$	V

LVPECL AC Switching Characteristics (Over Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
T_r / T_f	Rise/Fall time	20% to 80%, Differential	-	-	475	ps
T_{DC}	Duty Cycle	Differential	47	-	53	%
J_{Phase}	RMS Phase Jitter from 12kHz - 20MHz	At 3.3V with SS1= SS0 = 1	-	0.5	-	ps
		At 2.5V with SS1= SS0 = 1	-	1	-	ps

HCSL Output Buffer Characteristics

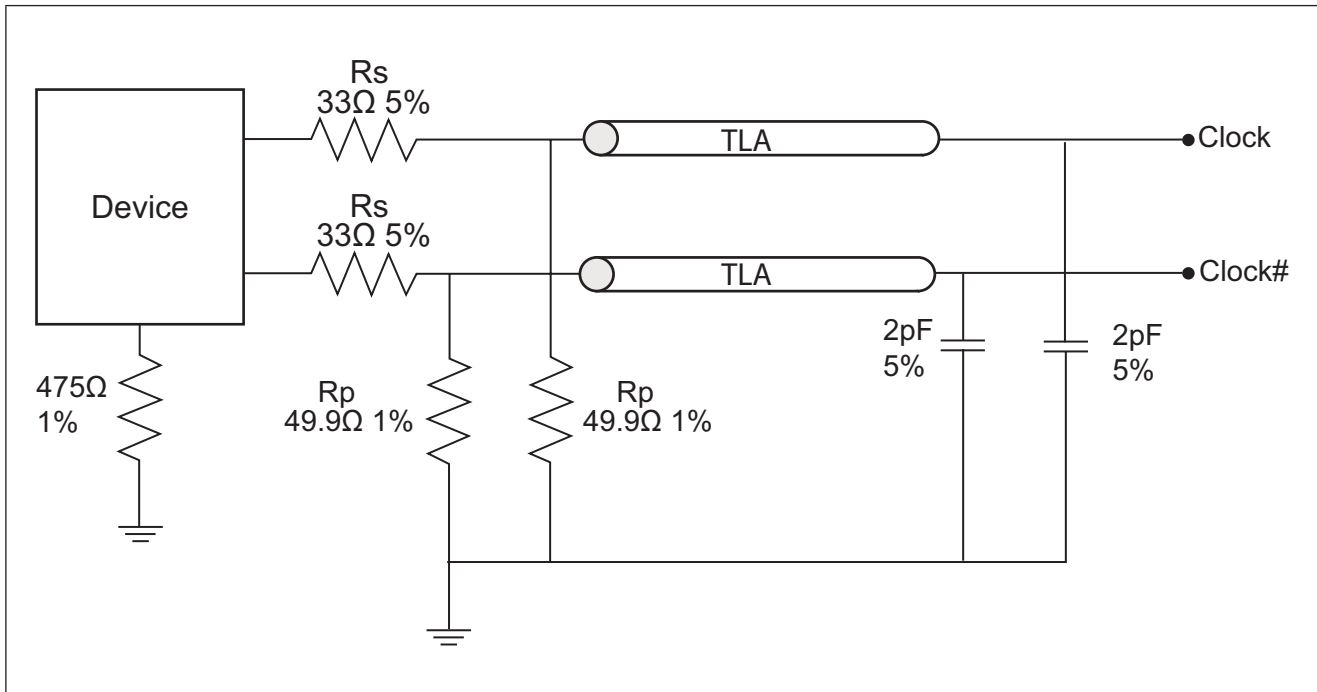


Simplified Diagram of Current-Mode Output Buffer

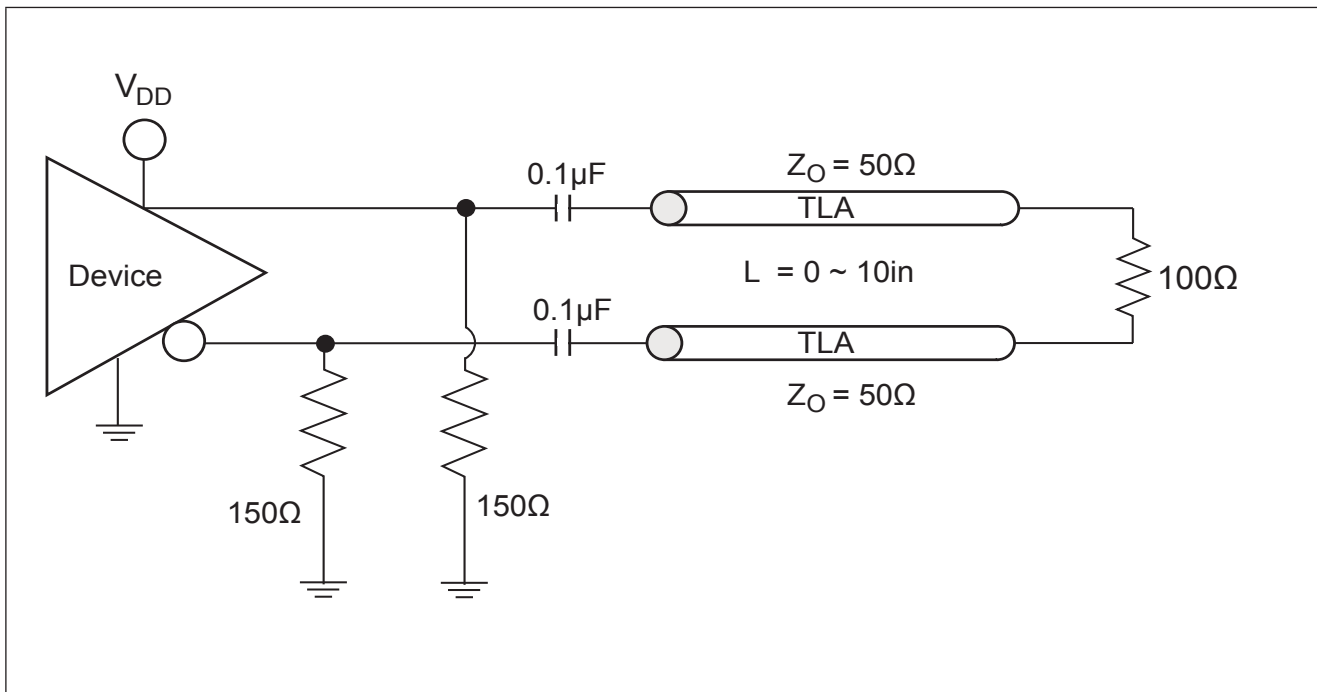
HCSL Output Buffer Characteristics

Symbol	Minimum	Maximum
RO	3000Ω	N/A
ROS	unspecified	unspecified
VOUT	N/A	850mV

Configuration Test Load Board Termination for HCSL Output



Configuration Test Load Board Termination for LVPECL Output

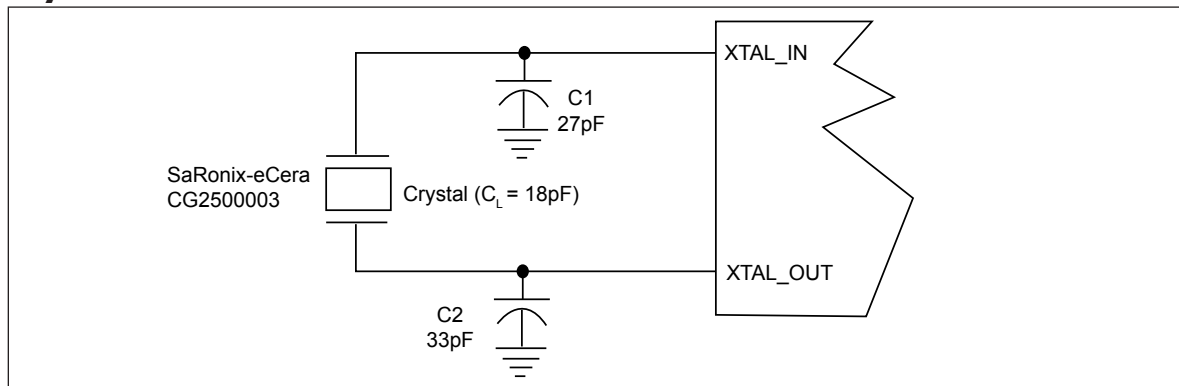


Application Notes

Crystal circuit connection

The following diagram shows PI6LC4833 crystal circuit connection with a parallel crystal. For the $CL=18pF$ crystal, it is suggested to use $C1=27pF$, $C2=33pF$. $C1$ and $C2$ can be adjusted to fine tune to the target ppm of crystal oscillator according to different board layouts.

Crystal Oscillator Circuit

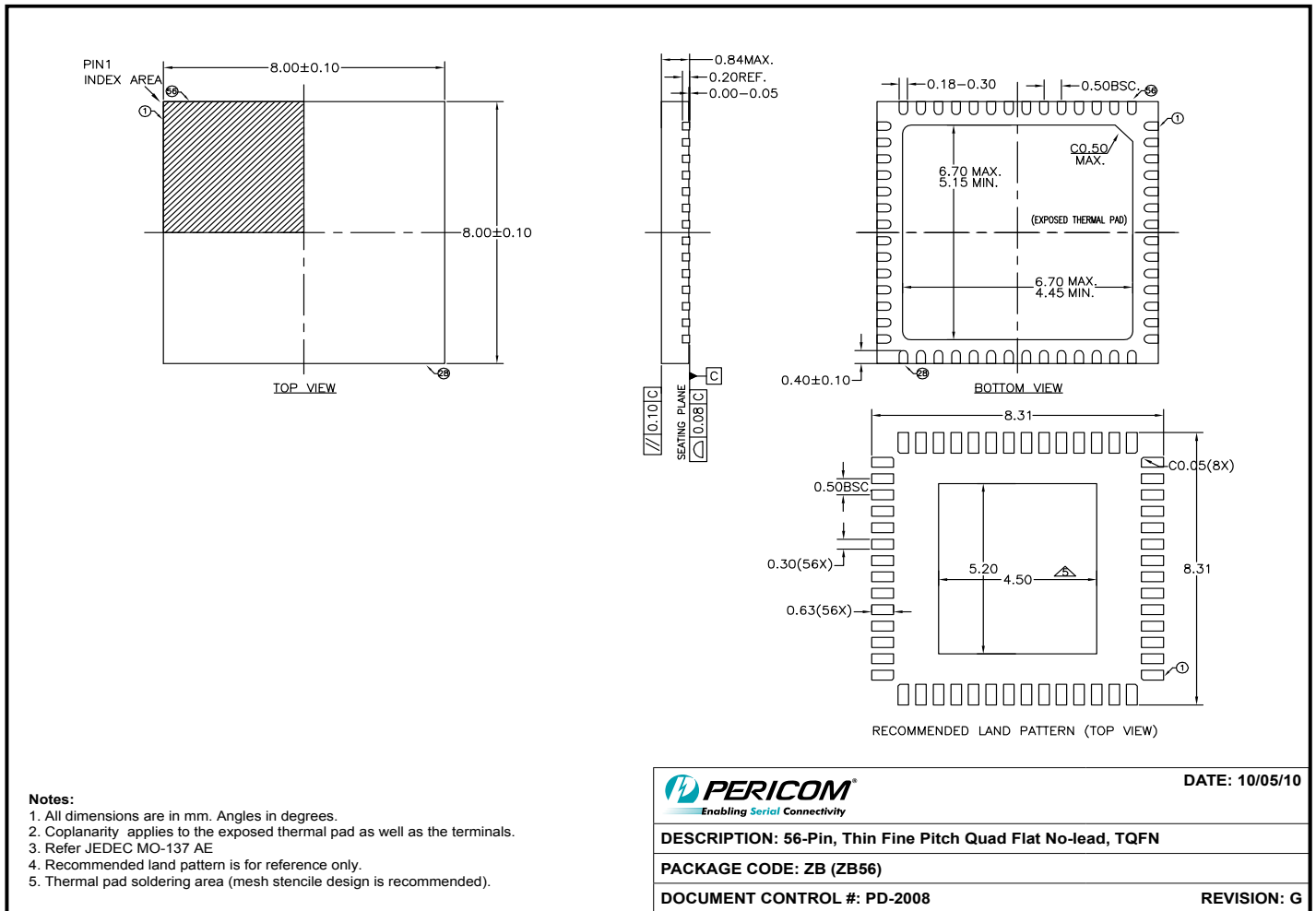


Recommended Crystal Specification

Pericom recommends:

- a) GC2500003 XTAL 49S/SMD(4.0 mm), 25M, $CL=18pF$, $\pm 30ppm$, http://www.pericom.com/pdf/datasheets/se/GC_GF.pdf
- b) FY2500081, SMD 5x3.2(4P), 25M, $CL=18pF$, $\pm 30ppm$, http://www.pericom.com/pdf/datasheets/se/FY_F9.pdf
- c) FL2500047, SMD 3.2x2.5(4P), 25M, $CL=18pF$, $\pm 20ppm$, <http://www.pericom.com/pdf/datasheets/se/FL.pdf>

Packaging Mechanical: 56-Pin TQFN (ZB)



Ordering Information

Ordering Code	Package Code	Package Type	Operating Temperature
PI6LC4833ZBIE	ZB	Pb-free & Green, 56-pin 315-mil wide TQFN	-40°C + 85°C

1. Thermal characteristics can be found on the company web site at www.pericom.com/packaging/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Diodes Incorporated:](#)

[PI6LC4833ZBIE](#)



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.